

REMARKS

Claims 1-32 remain in this application.

Entry of the above amendments is earnestly solicited.
An early and favorable first action on the merits is earnestly requested.

Should there be any matters that need to be resolved in the present application, the Examiner is respectfully requested to contact the undersigned at the telephone number listed below.

The Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 25-0120 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17.

Respectfully submitted,

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APPENDIX:

The Appendix includes the following item(s):

- a new Abstract of the Disclosure

ABSTRACT OF THE DISCLOSURE

A silicon carbon nitride film is formed on an interlayer dielectric film having Si-H bonds and a Cu interconnection. The silicon carbon nitride film has the role of blocking moisture absorption and prevents deterioration associated with the moisture absorption by a lower-layer insulating film and a Cu film, thereby suppressing an increase in the capacitance between interconnections or via resistance. The effect is great especially when the nitrogen concentration of the silicon carbon nitride film is not less than 10 atm % but less than 35 atm %. Between the interlayer dielectric film having Si-H bonds and the Cu interconnection is interposed a laminated film of a Ta film and a TaN film as a barrier metal film in such a manner that the TaN film becomes on the side of the interlayer dielectric film.